

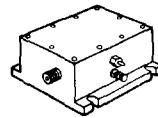
The RF Line Linear Power Amplifier

... designed for wideband linear applications in the 10 to 1000 MHz frequency range. This solid state, Class A amplifier incorporates microstrip circuit technology and high performance, gold metallized transistors to provide a complete broadband, linear amplifier operating from a supply voltage of 28 volts.

- Specified V_{CC} = 28 Volt and T_C = 25°C Characteristics:
 - Frequency Range — 10 to 1000 MHz
 - Output Power — 0.8 W Typ @ 1 dB Gain Compression, f = 500 MHz
 - Power Gain — 15 dB Typ @ f = 100 MHz
 - ITO — 42 dBm Typ @ f = 1000 MHz
 - Noise Figure — 8.5 dB Typ @ f = 1000 MHz
- 50 Ohm Input/Output Impedance
- Heavy Duty Machined Housing
- Gold Metallized Transistors for Improved Reliability
- Moisture Resistant, EMI Shielded Package

SHP10-15-08

**0.8 WATT
10-1000 MHz
LINEAR
POWER
AMPLIFIER**



**SHP
CASE 389A-01, STYLE 1**

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Supply Voltage	V_{CC}	32	Vdc
RF Power Input	P_{in}	20	dBm
Storage Temperature Range	T_{stg}	-55 to +100	°C
Operating Temperature Range	T_C	-40 to +85	°C

ELECTRICAL CHARACTERISTICS (T_C = 25°C, V_{CC} = 28 V, 50 Ω system unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Supply Current (V_{CC} = 28 V)	I_{CC}	360	400	440	mA
Power Gain (f = 100 MHz)	G_P	14	15	16	dB
Bandwidth	BW	10	—	1000	MHz
Gain Flatness (P-P) (f = 10-1000 MHz)	—	—	±0.5	±1	dB
Input/Output VSWR (f = 40-900 MHz) (f = 10-1000 MHz)	—	—	—	2:1 2.5:1	—
Output Power @ 1 dB Gain Compression (f = 500 MHz) (f = 1000 MHz)	$P_{o 1dB}$	28 27	29 28	—	dBm
Third Order Intercept Point (f = 500 MHz) (f = 1000 MHz)	ITO	41 40	43 42	—	dBm
Noise Figure (f = 500 MHz) (f = 1000 MHz)	NF	—	7.5 8.5	8.5 9.5	dB